

# International IOR Rectifier

PD -94313C

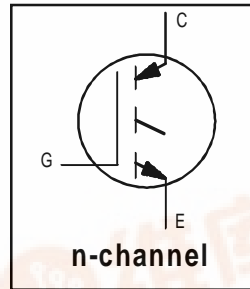
## IRG4MC30F

INSULATED GATE BIPOLAR TRANSISTOR

Fast Speed IGBT

### Features

- Electrically Isolated and Hermetically Sealed
- Simple Drive Requirements
- Latch-proof
- Fast Speed operation 3 kHz - 8 kHz
- High operating frequency
- Switching-loss rating includes all "tail" losses
- Ceramic eyelets



$V_{CES} = 600V$
$V_{CE(on) max} = 1.7V$
@ $V_{GE} = 15V, I_C = 15A$

### Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent IR Hi-Rel Generation 3 IGBT's

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	28	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	15	
$I_{CM}$	Pulsed Collector Current ①	112	
$I_{LM}$	Clamped Inductive Load Current ②	112	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	75	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	30	
$T_J$	Operating Junction and Storage Temperature Range	-55 to + 150	$^\circ C$
$T_{STG}$			
	Lead Temperature	300 (0.063in./1.6mm from case for 10s)	
	Weight	9.3 (typical)	g

### Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
$R_{thJC}$	Junction-to-Case	—	—	1.67	$^\circ C/W$	



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## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

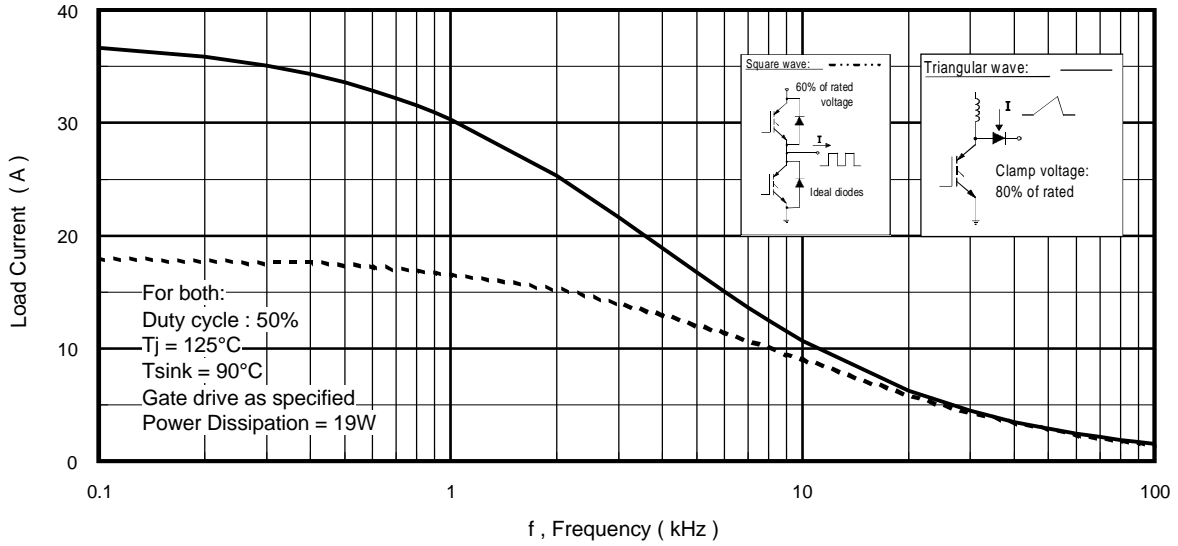
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 1.0 \text{ mA}$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ③	18	—	—	V	$V_{GE} = 0V, I_C = 1.0 \text{ A}$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.63	—	$V/^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0 \text{ mA}$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	—	1.7	V	$I_C = 15A, V_{GE} = 15V$
		—	—	2.2		$I_C = 28A$ See Fig.2, 5
		—	—	2.7		$I_C = 15A, T_J = 125^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 1.0 \text{ mA}$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	$\text{mV}/^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250 \mu\text{A}$
$g_{fe}$	Forward Transconductance ④	14	—	—	S	$V_{CE} \geq 15V, I_C = 15A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	50	$\mu\text{A}$	$V_{GE} = 0V, V_{CE} = 480V$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 480V, T_J = 125^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

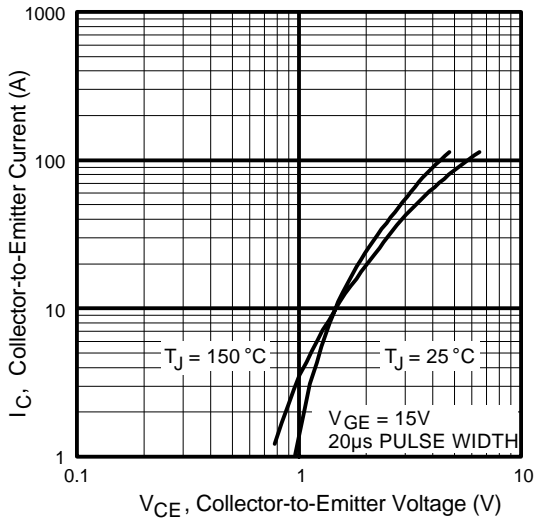
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	—	77	nC	$I_C = 15A$
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	—	12		$V_{CC} = 300V$ See Fig. 8
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	—	24		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	—	42	ns	$T_J = 25^\circ\text{C}$
$t_r$	Rise Time	—	—	30		$I_C = 15A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	—	300		$V_{GE} = 15V, R_G = 7.5\Omega$
$t_f$	Fall Time	—	—	300		Energy losses include "tail"
$E_{ts}$	Total Switching Loss	—	—	2.0	mJ	See Fig. 10, 11, 13, 14
$t_{d(on)}$	Turn-On Delay Time	—	—	25	ns	$T_J = 125^\circ\text{C}$ ,
$t_r$	Rise Time	—	—	20		$I_C = 15A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	—	450		$V_{GE} = 15V, R_G = 7.5\Omega$
$t_r$	Rise Time	—	—	550		Energy losses include "tail"
$E_{ts}$	Total Switching Loss	—	—	3.0	mJ	See Fig. 13, 14
$L_C+L_E$	Total Inductance	—	6.8	—	nH	Measured from Collector lead (6mm/0.25in. from package) to Emitter lead (6mm / 0.25in. from package)
$C_{ies}$	Input Capacitance	—	1100	—	pF	$V_{GE} = 0V$
$C_{oes}$	Output Capacitance	—	74	—		$V_{CC} = 30V$ See Fig. 7
$C_{res}$	Reverse Transfer Capacitance	—	14	—		$f = 1.0\text{MHz}$

### Notes:

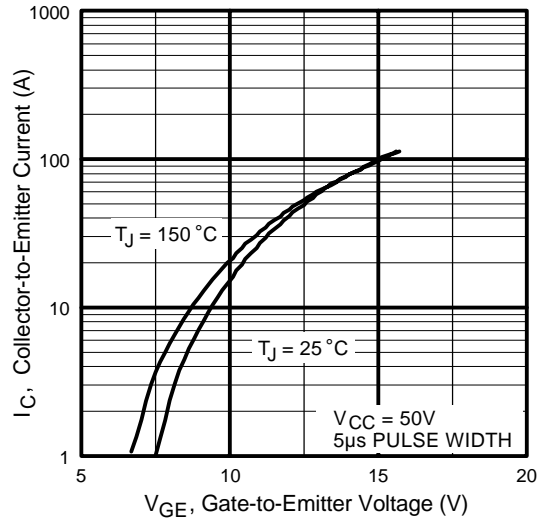
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 100\mu\text{H}, R_G = 7.5\Omega$ , (See fig. 13a)
- ③ Pulse width  $\leq 80\mu\text{s}$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu\text{s}$ , single shot.



**Fig. 1** - Typical Load Current vs. Frequency  
 (For square wave,  $I = I_{RMS}$  of fundamental; for triangular wave,  $I = I_{PK}$ )



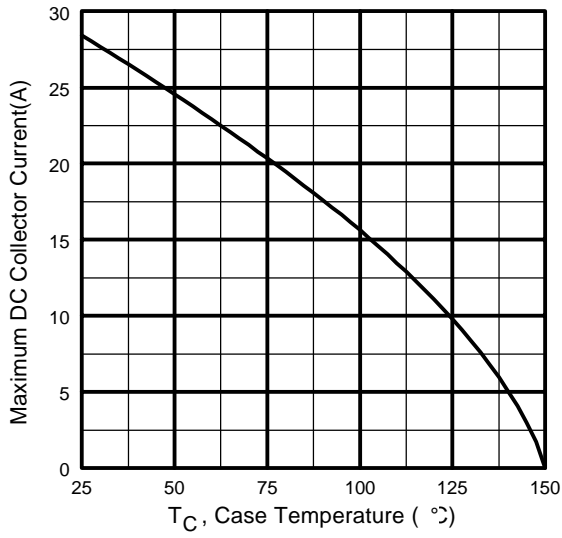
**Fig. 2** - Typical Output Characteristics



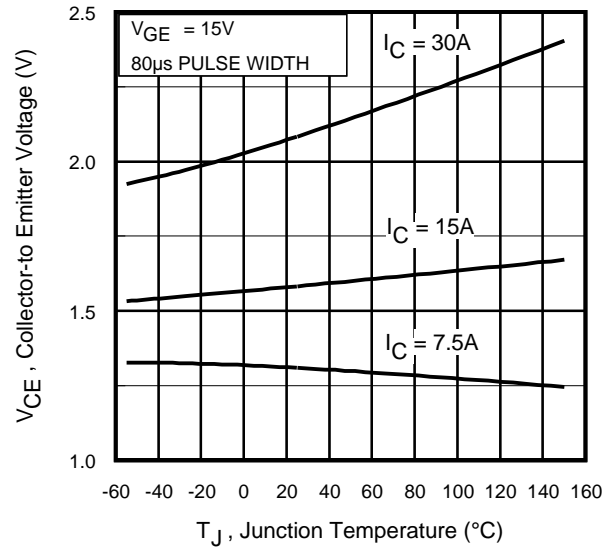
**Fig. 3** - Typical Transfer Characteristics

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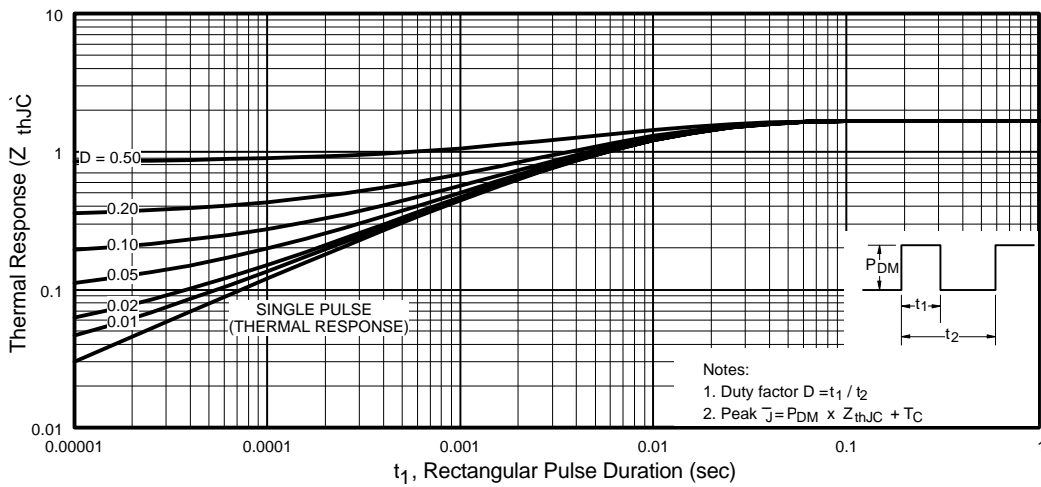
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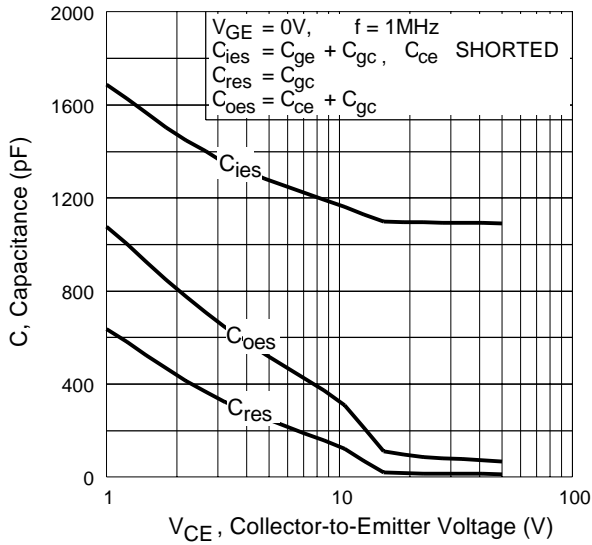
**Fig. 4** - Maximum Collector Current vs. Case Temperature



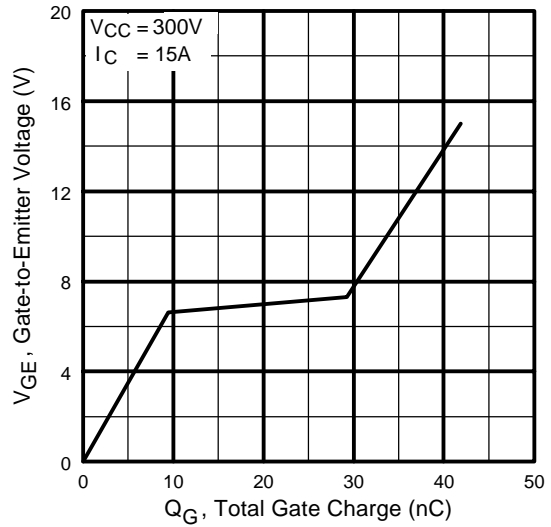
**Fig. 5** - Collector-to-Emitter Voltage vs. Junction Temperature



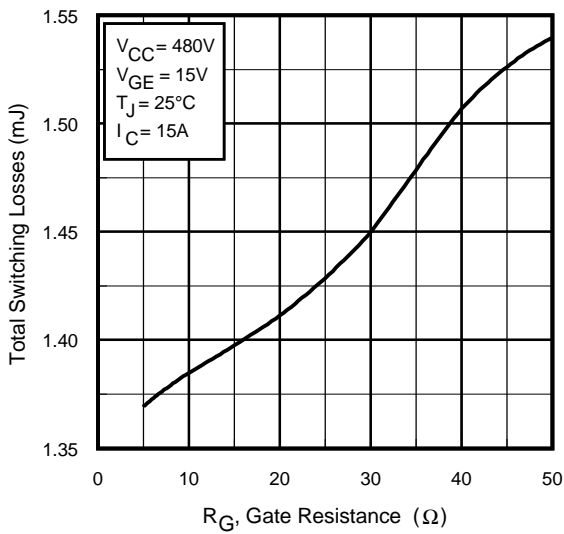
**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case



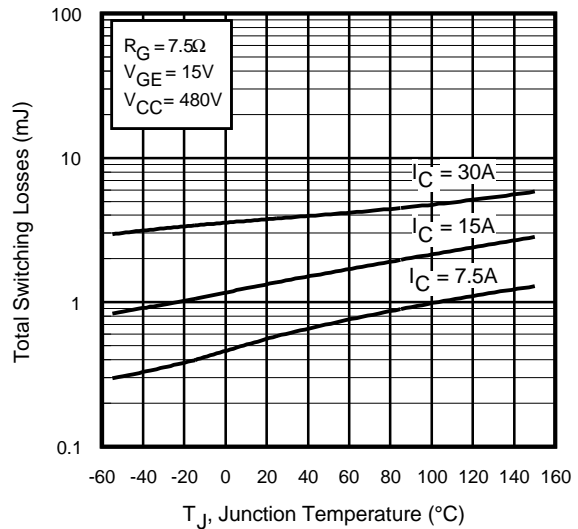
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



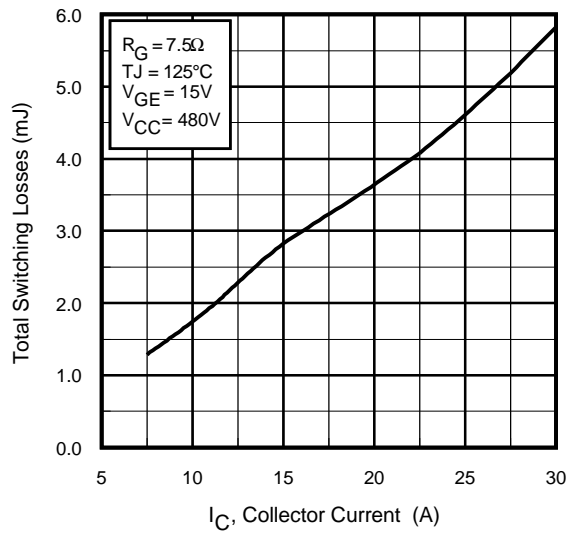
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



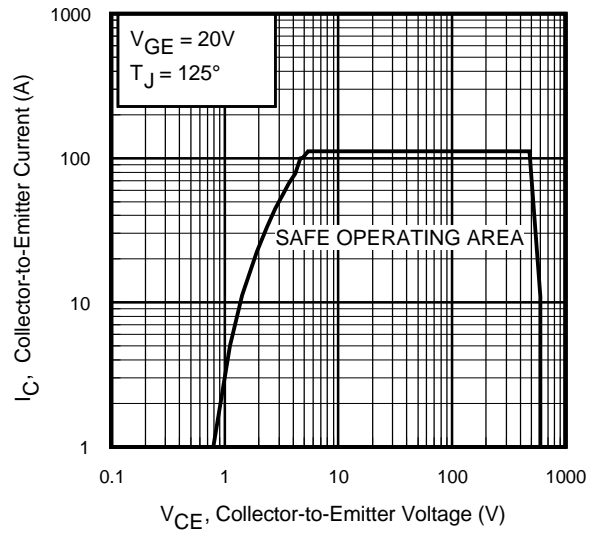
**Fig. 10** - Typical Switching Losses vs. Junction Temperature

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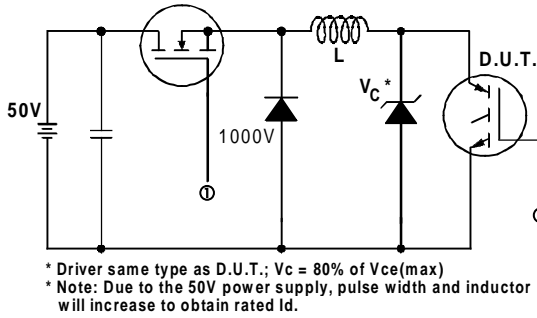
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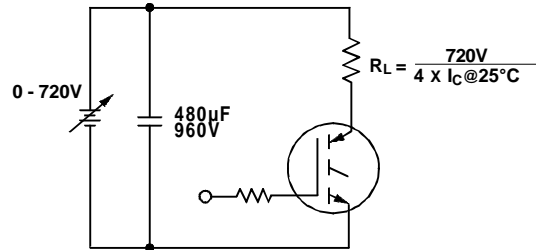
**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



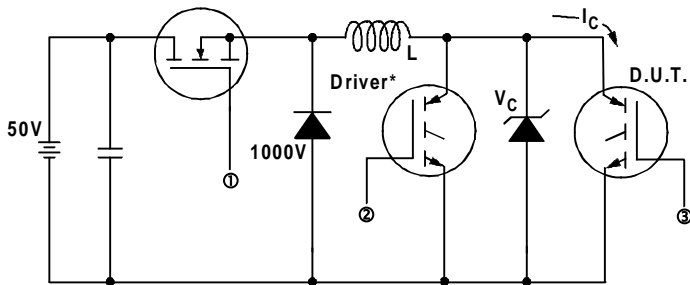
**Fig. 12** - Turn-Off SOA



**Fig. 13a** - Clamped Inductive Load Test Circuit

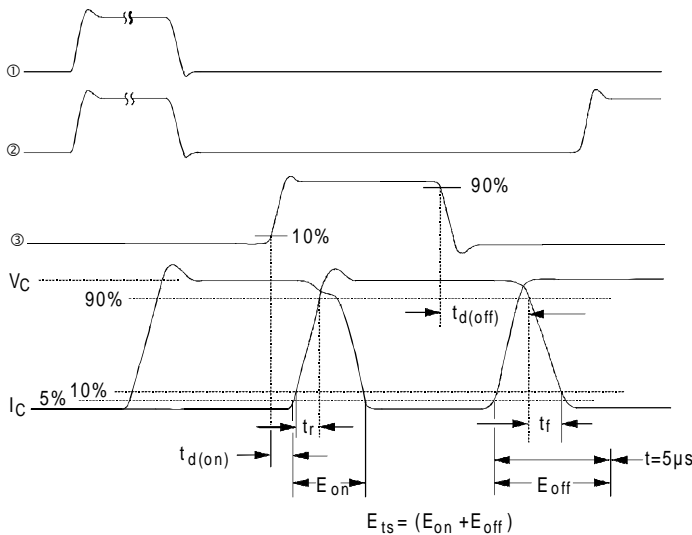


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T.,  $V_C = 720V$

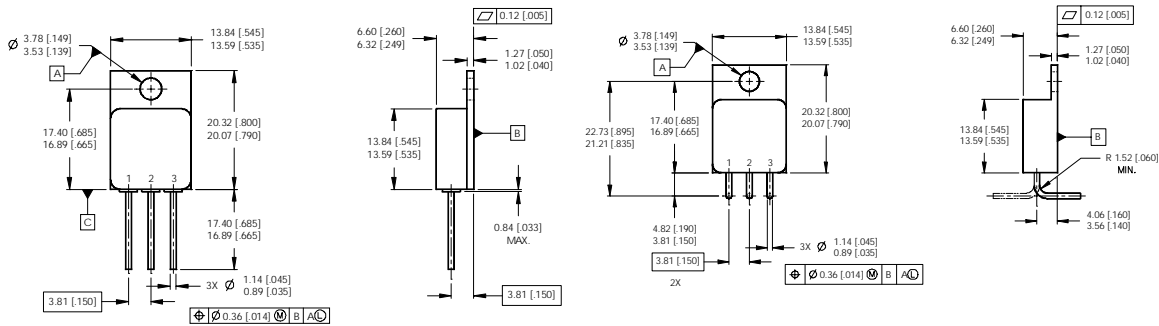


**Fig. 14b** - Switching Loss Waveforms

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## Case Outline and Dimensions — TO-254AA



### NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. CONFORMS TO JEDEC OUTLINE TO-254AA.

### PIN ASSIGNMENTS

- 1=COLLECTOR
- 2=EMITTER
- 3=GATE

### CAUTION

#### BERYLLIA WARNING PER MIL-PRF-19500

Packages containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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